

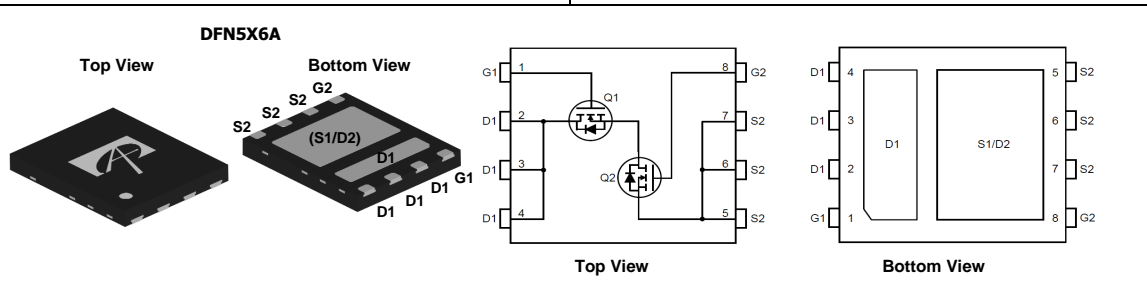
General Description

The AON6922 is designed to provide a high efficiency synchronous buck power stage with optimal layout and board space utilization. It includes two specialized MOSFETs in a dual Power DFN5x6A package. The Q1 "High Side" MOSFET is designed to minimize switching losses. The Q2 "Low Side" MOSFET is designed for low $R_{DS(ON)}$ to reduce conduction losses. The AON6922 is well suited for use in compact DC/DC converter applications.

Product Summary

	Q1	Q2
V_{DS}	25V	25V
I_D (at $V_{GS}=10V$)	71A	85A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	<3.8m Ω	<1.4m Ω
$R_{DS(ON)}$ (at $V_{GS} = 4.5V$)	<4.8m Ω	<1.8m Ω

100% UIS Tested
 100% Rg Tested



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Max Q1	Max Q2	Units
Drain-Source Voltage	V_{DS}	25		V
Gate-Source Voltage	V_{GS}	± 12		V
Continuous Drain Current ^G	I_D	71	85	A
$T_C=100^\circ\text{C}$		44	66	
Pulsed Drain Current ^C	I_{DM}	240	420	A
Continuous Drain Current	I_{DSM}	18	31	A
$T_A=70^\circ\text{C}$		14	25	
Avalanche Current ^C	I_{AS}, I_{AR}	40	78	A
Avalanche Energy $L=0.1\text{mH}$ ^C	E_{AS}, E_{AR}	80	304	mJ
Power Dissipation ^B	P_D	31	104	W
$T_C=100^\circ\text{C}$		12.5	41.5	
Power Dissipation ^A	P_{DSM}	2	2.2	W
$T_A=70^\circ\text{C}$		1.3	1.4	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150		$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ Q1	Typ Q2	Max Q1	Max Q2	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	25	20	30	25	$^\circ\text{C/W}$
$t \leq 10\text{s}$		50	45	60	55	
Maximum Junction-to-Ambient ^{A,D}	$R_{\theta JC}$	3.1	0.9	4	1.2	$^\circ\text{C/W}$
Steady-State						

Q1 Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	25			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =25V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±12V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.7	1.2	1.7	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	240			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A T _J =125°C		3 4.3	3.8 5.4	mΩ
		V _{GS} =4.5V, I _D =20A		3.7	4.8	
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		125		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.7	1	V
I _S	Maximum Body-Diode Continuous Current				30	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =12.5V, f=1MHz	1560	1950	2340	pF
C _{oss}	Output Capacitance		530	755	980	pF
C _{riss}	Reverse Transfer Capacitance		20	70	120	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.7	1.4	2.1	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =12.5V, I _D =20A	21	26.5	32	nC
Q _{g(4.5V)}	Total Gate Charge		9	11.2	13.4	nC
Q _{gs}	Gate Source Charge			2.7		nC
Q _{gd}	Gate Drain Charge			4		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =12.5V, R _L =1.25Ω, R _{GEN} =3Ω		5.5		ns
t _r	Turn-On Rise Time			3.5		ns
t _{D(off)}	Turn-Off DelayTime			30		ns
t _f	Turn-Off Fall Time			4		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, dI/dt=500A/μs	12	15	18	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, dI/dt=500A/μs	20	25	30	nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_{DSM} is based on R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150°C. The SOA curve provides a single pulse rating g.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in2 FR-4 board with 2oz. Copper, in a still air environment with TA=25°C.

COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

Q1-CHANNEL: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

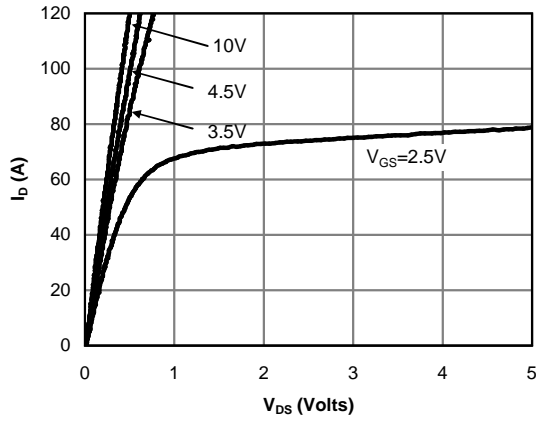


Fig 1: On-Region Characteristics (Note E)

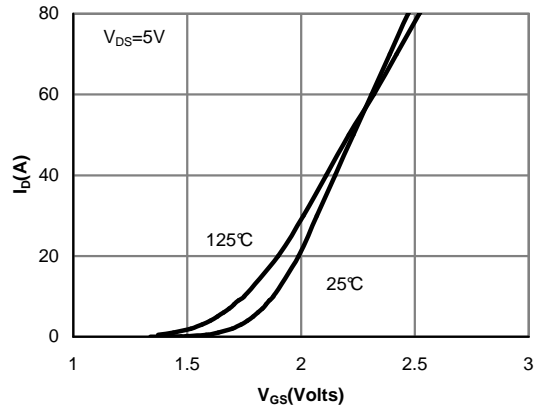


Figure 2: Transfer Characteristics (Note E)

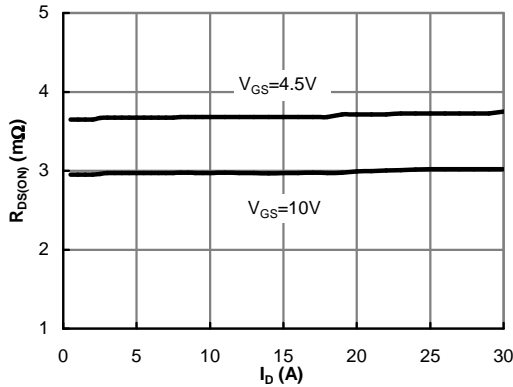


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

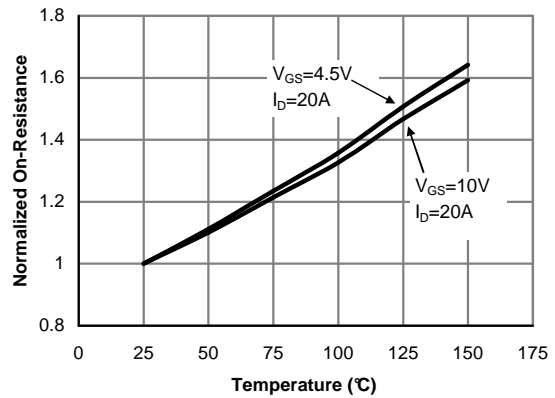


Figure 4: On-Resistance vs. Junction Temperature (Note E)

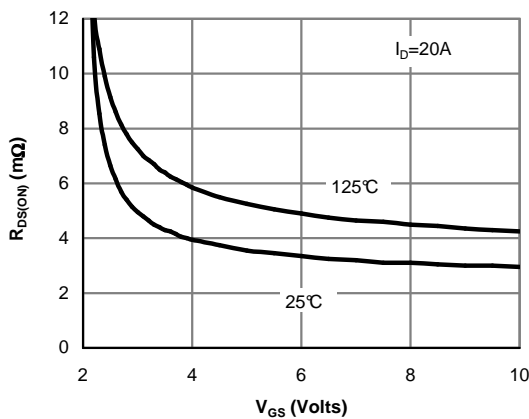


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

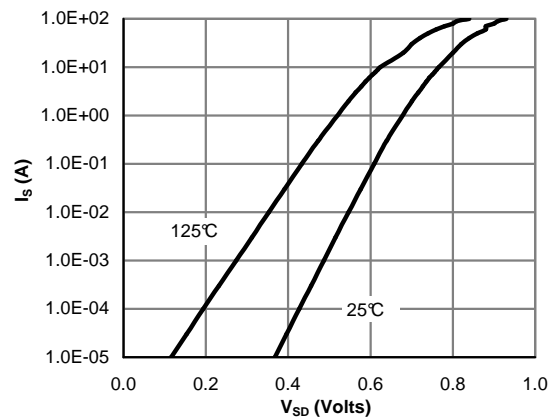


Figure 6: Body-Diode Characteristics (Note E)

Q1-CHANNEL: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

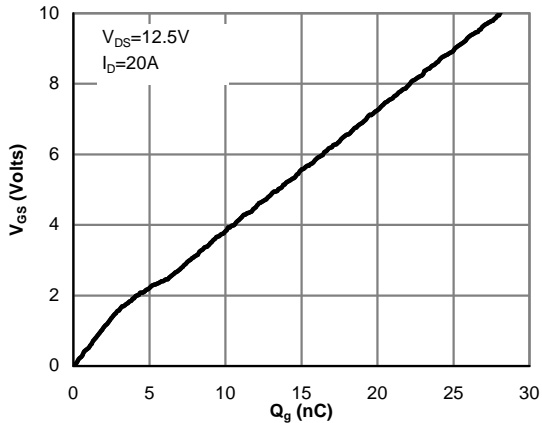


Figure 7: Gate-Charge Characteristics

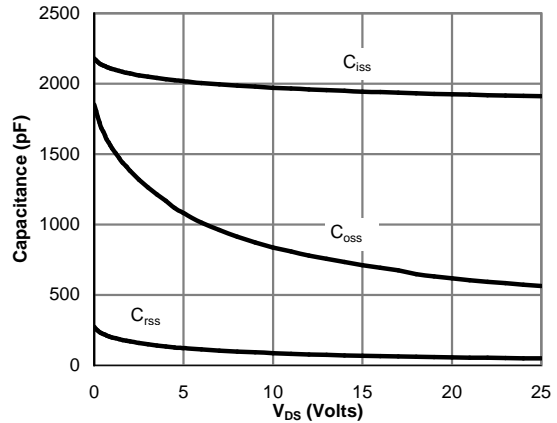


Figure 8: Capacitance Characteristics

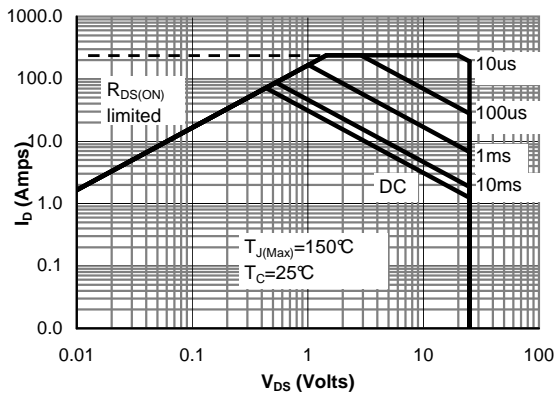


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

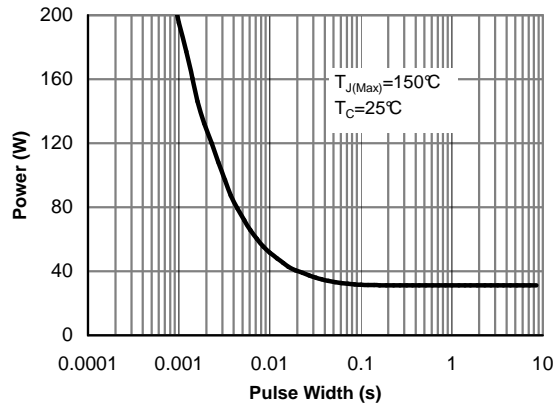


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

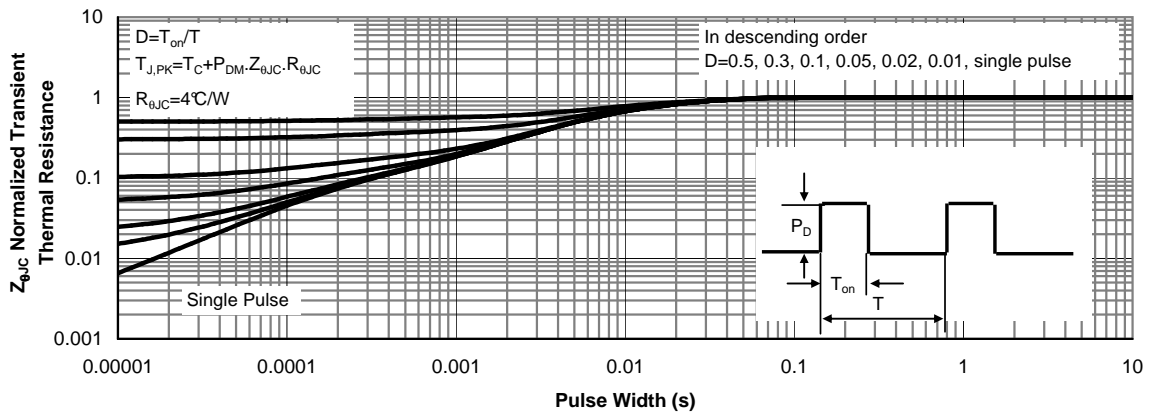


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Q1-CHANNEL: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

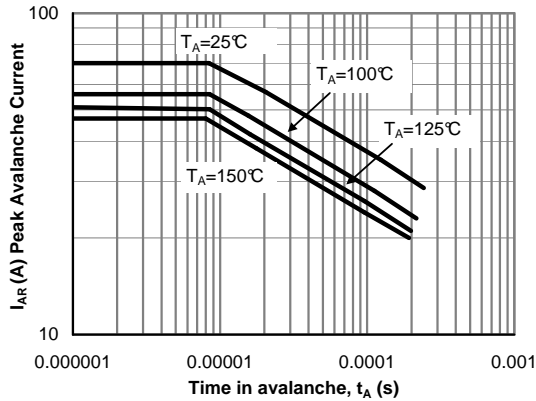


Figure 12: Single Pulse Avalanche capability (Note C)

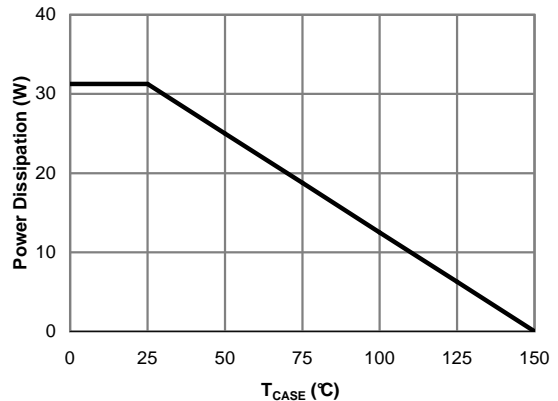


Figure 13: Power De-rating (Note F)

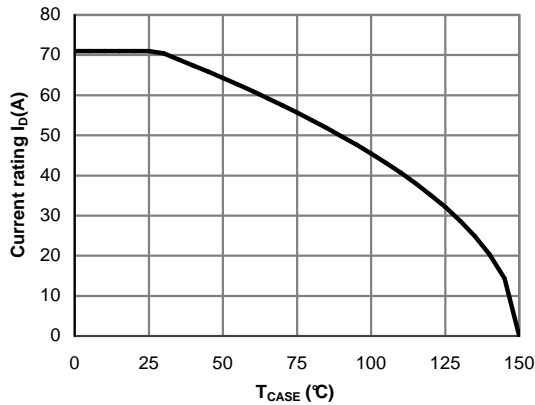


Figure 14: Current De-rating (Note F)

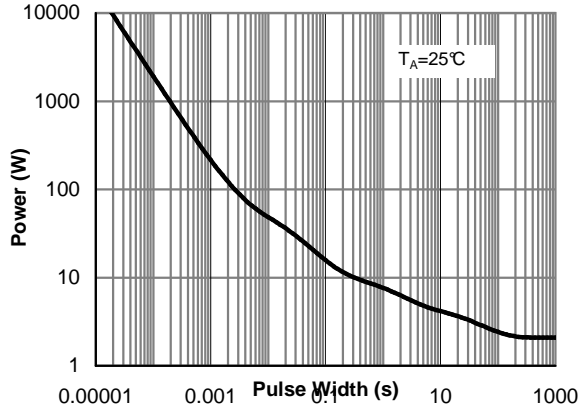


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

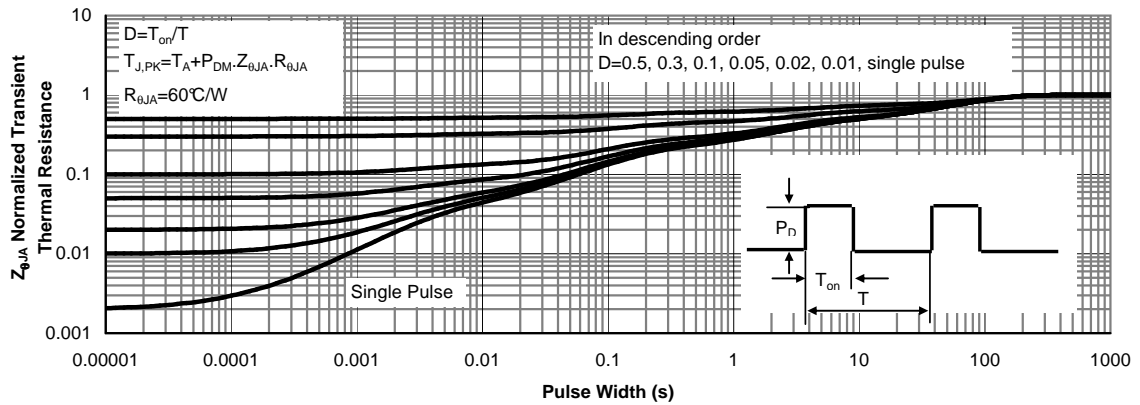


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

Q2 Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	25			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =25V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±12V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.7	1.2	1.7	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	420			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A T _J =125°C		1.15 1.6	1.4 2	mΩ
		V _{GS} =4.5V, I _D =20A		1.4	1.8	
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		135		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.65	1	V
I _S	Maximum Body-Diode Continuous Current ^G				85	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =12.5V, f=1MHz	4550	5690	6830	pF
C _{oss}	Output Capacitance		1730	2470	3210	pF
C _{riss}	Reverse Transfer Capacitance		50	165	280	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.4	0.8	1.2	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =12.5V, I _D =20A	52	65	78	nC
Q _{g(4.5V)}	Total Gate Charge		20	26	32	nC
Q _{gs}	Gate Source Charge			7.4		nC
Q _{gd}	Gate Drain Charge			5.7		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =12.5V, R _L =0.6Ω, R _{GEN} =3Ω		9		ns
t _r	Turn-On Rise Time			4.5		ns
t _{D(off)}	Turn-Off DelayTime			60		ns
t _f	Turn-Off Fall Time			8		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, dI/dt=500A/μs	19	24.5	30	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, dI/dt=500A/μs	55	68	82	nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The Power dissipation P_{DSM} is based on R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J=25°C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150°C. The SOA curve provides a single pulse rating g.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

Q2-CHANNEL: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

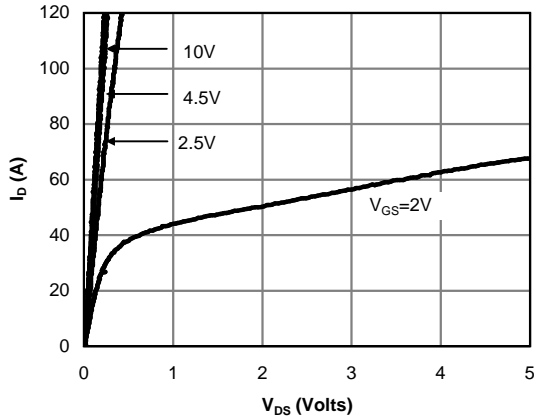


Fig 1: On-Region Characteristics (Note E)

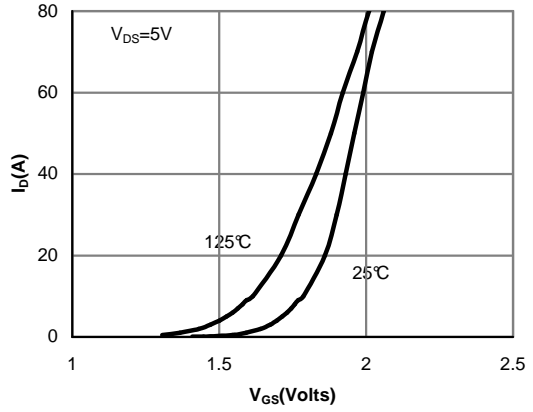


Figure 2: Transfer Characteristics (Note E)

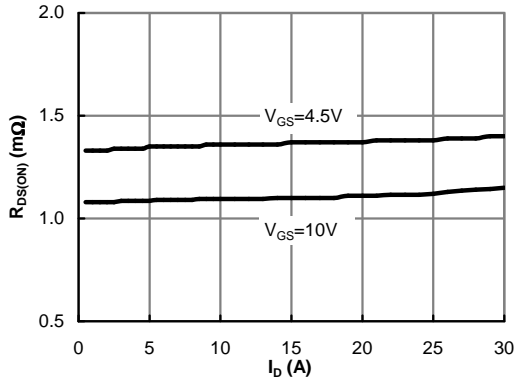


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

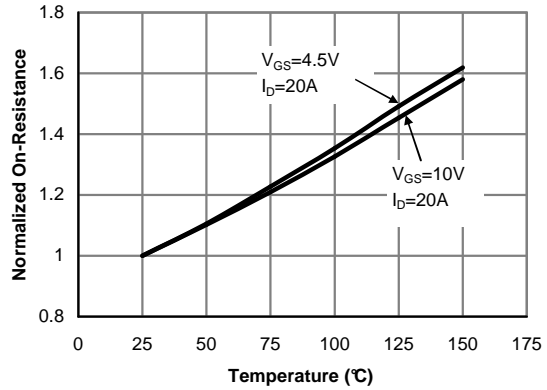


Figure 4: On-Resistance vs. Junction Temperature (Note E)

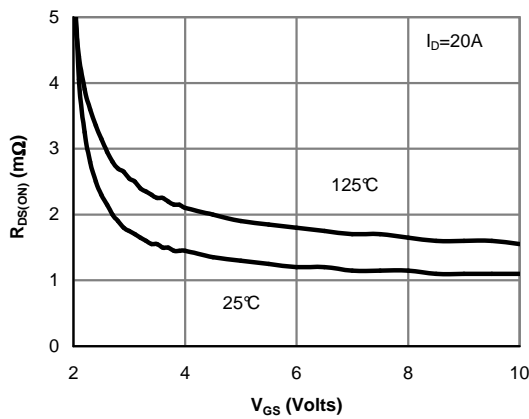


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

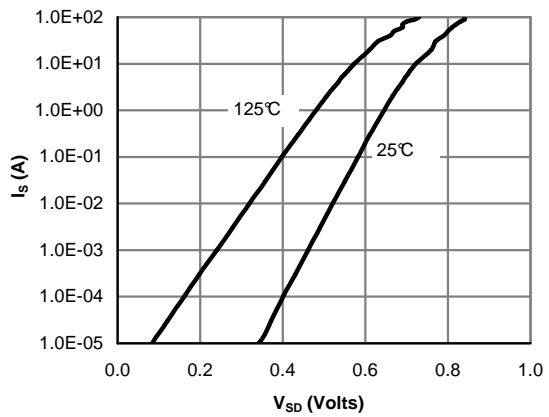


Figure 6: Body-Diode Characteristics (Note E)

Q2-CHANNEL: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

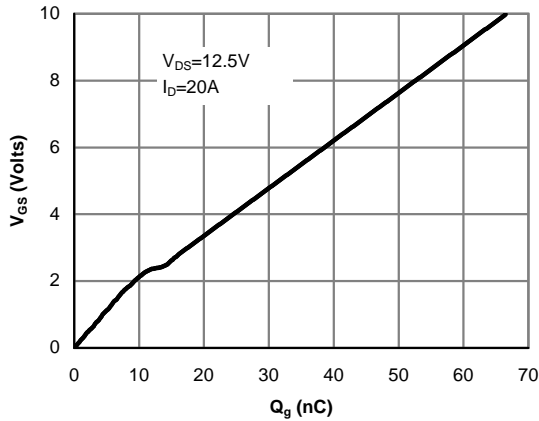


Figure 7: Gate-Charge Characteristics

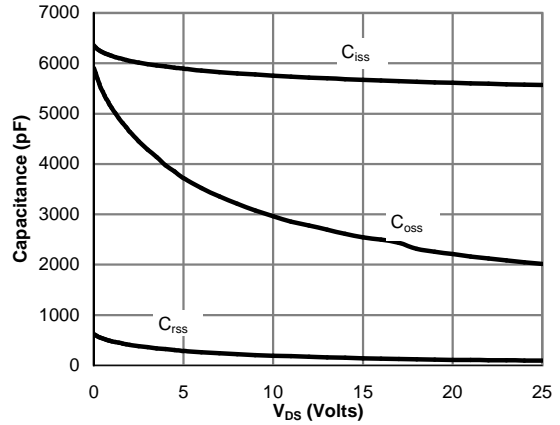


Figure 8: Capacitance Characteristics

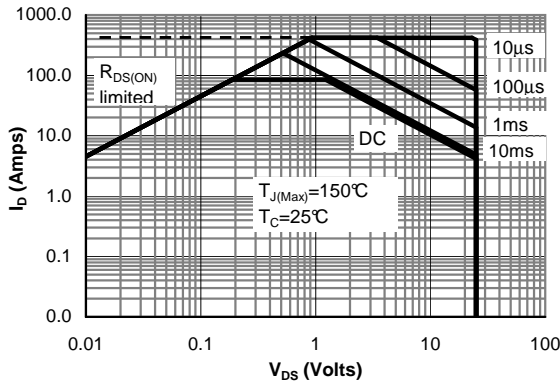


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

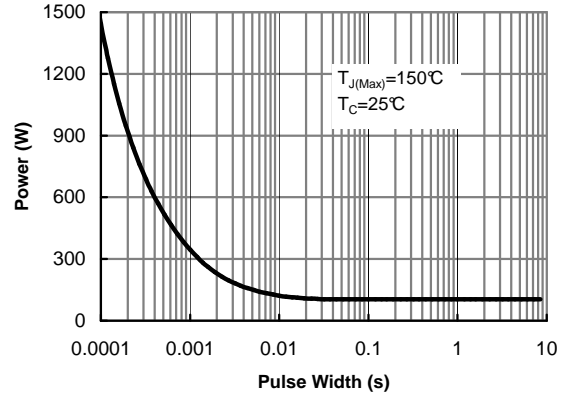


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

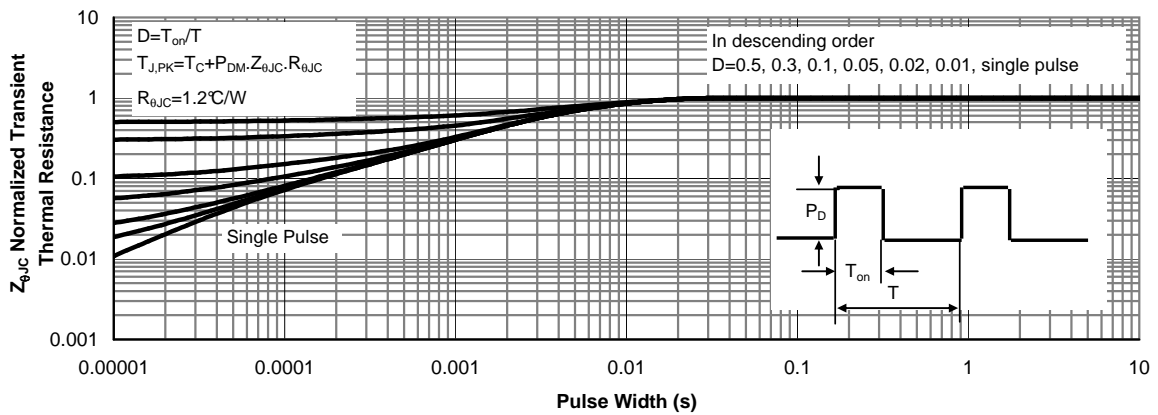


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Q2-CHANNEL: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

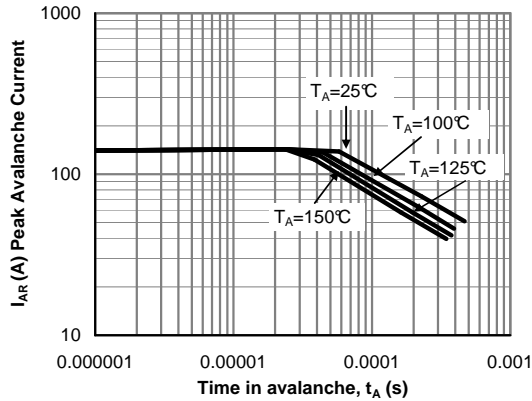


Figure 12: Single Pulse Avalanche capability (Note C)

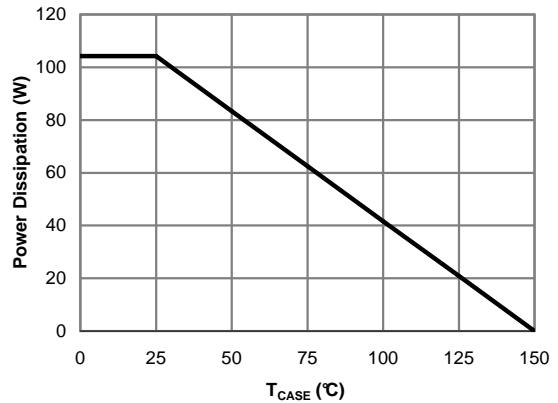


Figure 13: Power De-rating (Note F)

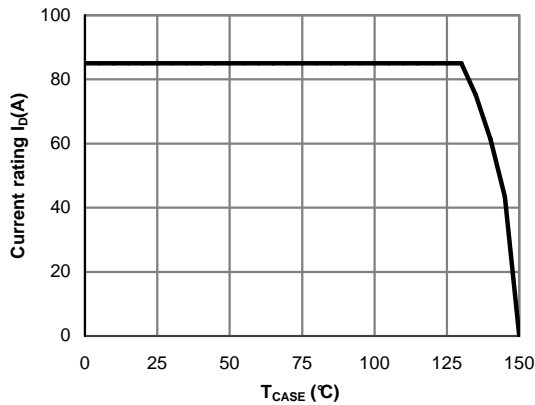


Figure 14: Current De-rating (Note F)

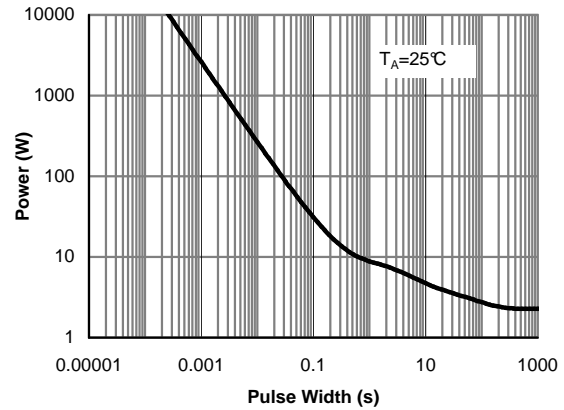


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note G)

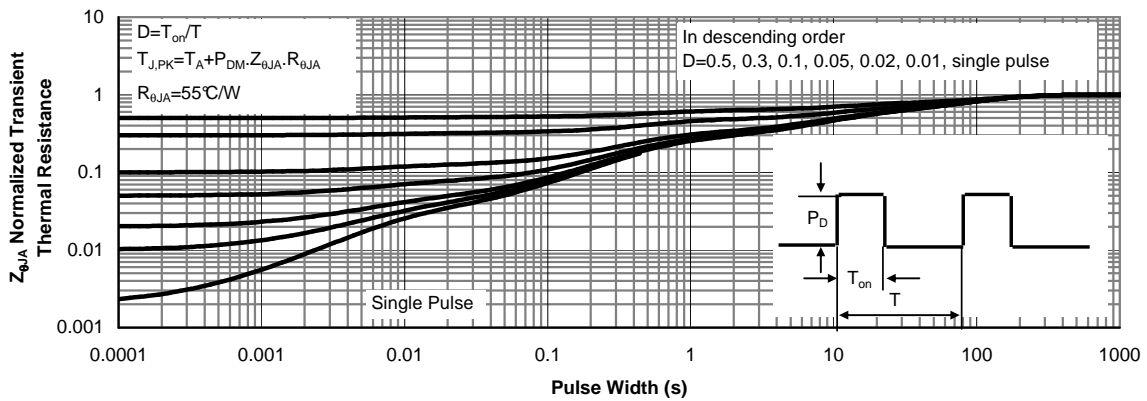
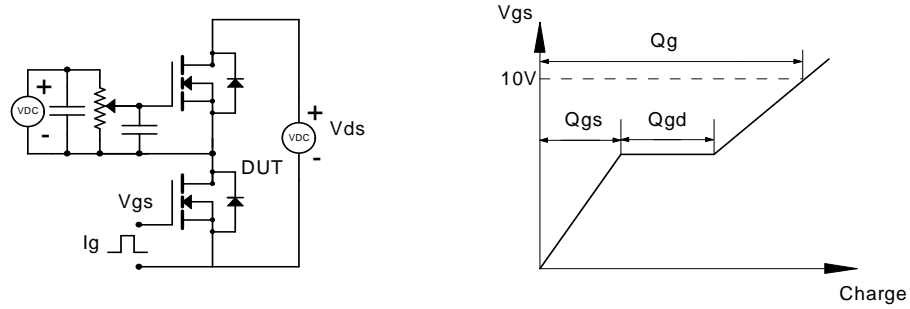
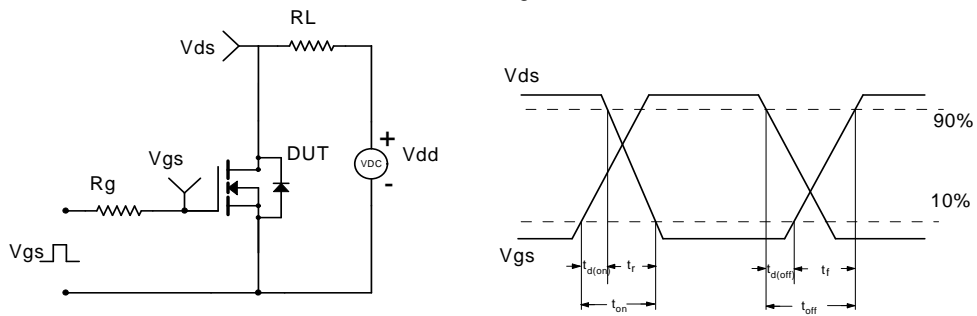


Figure 16: Normalized Maximum Transient Thermal Impedance (Note G)

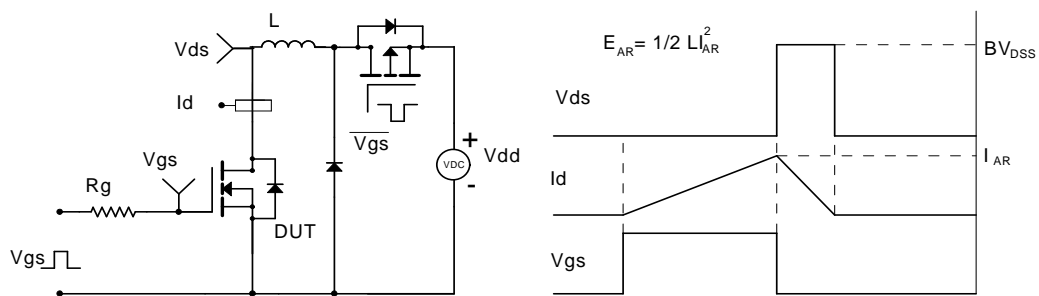
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

